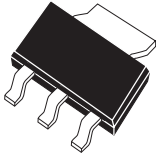


CZTA44

NPN SILICON EXTREMELY HIGH VOLTAGE TRANSISTOR



SOT-223 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CZTA44 type is a surface mount epoxy molded silicon planar epitaxial transistors designed for extremely high voltage applications.

MAXIMUM RATINGS (T_A=25°C)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Collector Current
Power Dissipation
Operating and Storage
Junction Temperature
Thermal Resistance

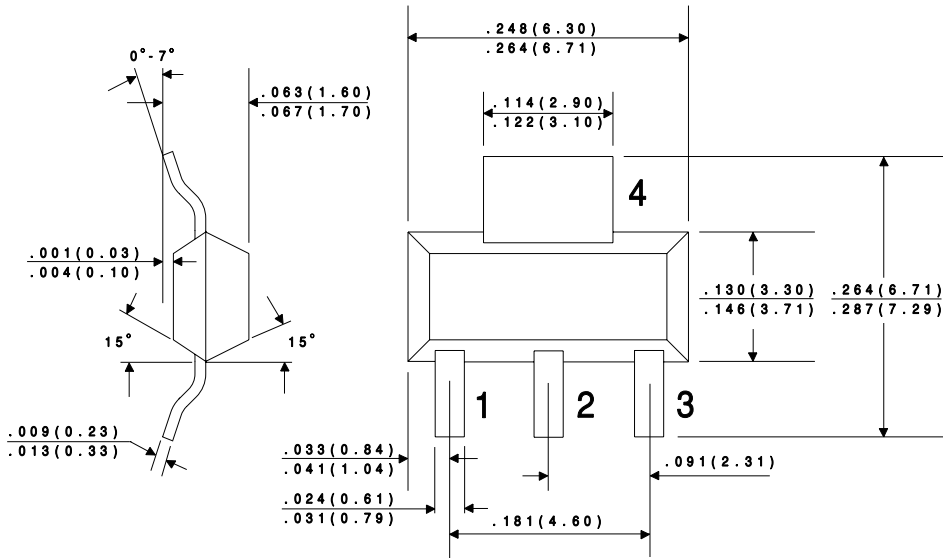
SYMBOL		UNITS
V _{CB0}	450	V
V _{CEO}	400	V
V _{EBO}	6.0	V
I _C	300	mA
P _D	2.0	W
T _J , T _{stg}	-65 to +150	°C
θ _{JA}	62.5	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{CB0}	V _{CB} =400V		100	nA
I _{CES}	V _{CE} =400V		500	nA
I _{EBO}	V _{BE} =4.0V		100	nA
BV _{CB0}	I _C =100μA	450		V
BV _{CES}	I _C =100μA	450		V
BV _{CEO}	I _C =1.0mA	400		V
BV _{EBO}	I _E =10μA	6.0		V
V _{CE(SAT)}	I _C =1.0mA, I _B =0.1mA		0.40	V
V _{CE(SAT)}	I _C =10mA, I _B =1.0mA		0.50	V
V _{CE(SAT)}	I _C =50mA, I _B =5.0mA		0.75	V
V _{BE(SAT)}	I _C =10mA, I _B =1.0mA		0.75	V
h _{FE}	V _{CE} =10V, I _C =1.0mA	40		
h _{FE}	V _{CE} =10V, I _C =10mA	50	200	
h _{FE}	V _{CE} =10V, I _C =50mA	45		

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
h_{FE}	$V_{CE}=10V, I_C=100mA$	20		
f_T	$V_{CE}=10V, I_C=10mA, f=10MHz$	20		MHz
C_{ob}	$V_{CB}=20V, I_E=0, f=1.0MHz$		7.0	pF
C_{ib}	$V_{EB}=0.5V, I_C=0, f=1.0MHz$		130	pF

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 4) COLLECTOR